Abstracts

A mixed Si and GaAs chip set for millimeter-wave automotive radar front-ends

H.J. Siweris, A. Werthof, H. Tischer, T. Grave, H. Werthmann, R.H. Rasshofer and W. Kellner. "A mixed Si and GaAs chip set for millimeter-wave automotive radar front-ends." 2000 Radio Frequency Integrated Circuits (RFIC) Symposium 00. (2000 [RFIC]): 191-194.

A chip set consisting of three GaAs HEMT MMICs (voltage-controlled oscillator, medium power amplifier, subharmonic mixer) and a discrete Si Schottky mixer diode has been developed for 77 GHz automotive radar systems. It facilitates the realization of a high performance millimeter-wave radar front-end with a minimum amount of chip area and, consequently, low production costs.

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